

IN THE ABSTRACT:

Please amend the Abstract of the Disclosure as shown below:

~~Integration of~~ A method for manufacturing high performance copper inductors ~~are provided~~ ~~wherein~~ includes providing a tall, Cu laminate spiral inductor is formed at the last metal level, and at the last metal + 1 level, with the metal levels being interconnected by a bar via having the same spiral shape as the spiral metal inductors at the last metal level and the last metal + 1 level. ~~The invention provides methods for~~ method includes integrating the formation of thick inductors with the formation of bond pads, terminals and interconnect wiring with the last metal + 1 wiring. ~~The subject invention uses~~ Included are dielectric deposition[[,]] and spacer formation steps, and/or selective deposition of a passivating metal such as CoWP, to passivate a Cu inductor that is formed after the last metal layer.